August 1993 Revised March 1999

74VHC125 Quad Buffer with 3-STATE Outputs

General Description

FAIRCHILD

SEMICONDUCTOR

The VHC125 contains four independent non-inverting buffers with 3-STATE outputs. It is an advanced high-speed CMOS device fabricated with silicon gate CMOS technology and achieves the high-speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

An input protection circuit insures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery backup. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High Speed: t_{PD} = 3.8 ns (typ) at V_{CC} = 5V
- \blacksquare Lower power dissipation: $I_{CC}=4~\mu A$ (max) at $T_A=25^\circ C$
- I High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Power down protection is provided on all inputs
- Low noise: V_{OLP} = 0.8V (max)

Ordering Code:

Order Number	Package Number	Package Description
74VHC125M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150 Narrow
74VHC125SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74VHC125MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
74VHC125N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide

Surface mount packages are also available on Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

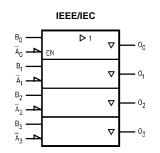
Logic Symbol

Pin Descriptions

 \overline{A}_n, B_n

On

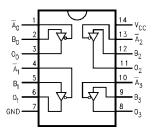
Pin Names



Description

Inputs Outputs

Connection Diagram



Function Table

Inp	uts	Output		
Ā _n	Ā _n B _n			
L	L	L		
L	н	н		
н	х	Z		

H = HIGH Voltage Level

L = LOW Voltage Level Z = HIGH Impedance

X = Immaterial

Absolute Maximum Ratings(Note 1)

Supply Voltage (V _{CC})	-0.5V to +7.0V
DC Input Voltage (V _{IN})	-0.5V to +7.0V
DC Output Voltage (V _{OUT})	-0.5V to V _{CC} + 0.5V
Input Diode Current (I _{IK})	–20 mA
Output Diode Current (I _{OK})	±20 mA
DC Output Current (I _{OUT})	±25 mA
DC V _{CC} /GND Current (I _{CC})	±50 mA
Storage Temperature (T _{STG})	-65°C to +150°C
Lead Temperature (T _L)	
(Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

Supply Voltage (V _{CC})	2.0V to +5.5V
Input Voltage (V _{IN})	0V to +5.5V
Output Voltage (V _{OUT})	0V to V_{CC}
Operating Temperature (T _{OPR})	$-40^{\circ}C$ to $+85^{\circ}C$
Input Rise and Fall Time (t_r, t_f)	
$V_{CC}=3.3V\pm0.3V$	0 ~ 100 ns/V
$V_{CC}=5.0V\pm0.5V$	0 ~ 20 ns/V

Note 1: Absolute Maximum Ratings are values beyond which the device may be damaged or have its useful life impaired. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. Fairchild does not recommend operation outside databook specifications.

Note 2: Unused inputs must be held HIGH or LOW. They may not float.

DC Electrical Characteristics

Symbol	Parameter	V _{cc}	V_{CC} $T_A = 25^{\circ}C$ $T_A = -40^{\circ}C \text{ to } +85^{\circ}C$ Units	Cor	Conditions						
Symbol	Farameter	(V)	Min	Тур	Max	Min	Max	Units	Conditions		
V _{IH}	HIGH Level Input	2.0	1.50			1.50		V			
	Voltage	3.0 - 5.5	0.7 V _{CC}			0.7 V _{CC}		v			
VIL	LOW Level Input	2.0			0.50		0.50	V			
	Voltage	3.0 - 5.5			0.3 V _{CC}		0.3 V _{CC}	v			
V _{OH}	HIGH Level Output	2.0	1.9	2.0		1.9			$V_{IN} = V_{IH}$	$I_{OH} = -50 \ \mu A$	
	Voltage	3.0	2.9	3.0		2.9		V	or V _{IL}		
		4.5	4.4	4.5		4.4					
		3.0	2.58			2.48		V		$I_{OH} = -4 \text{ mA}$	
		4.5	3.94			3.80		v		$I_{OH} = -8 \text{ mA}$	
V _{OL}	LOW Level Output	2.0		0.0	0.1		0.1		$V_{IN} = V_{IH}$	$I_{OL} = 50 \ \mu A$	
	Voltage	3.0		0.0	0.1		0.1	V	or V _{IL}		
		4.5		0.0	0.1		0.1				
		3.0			0.36		0.44	V		$I_{OL} = 4 \text{ mA}$	
		4.5			0.36		0.44	v		$I_{OL} = 8 \text{ mA}$	
I _{OZ}	3-STATE Output	5.5			±0.25		±2.5	μΑ	$V_{IN} = V_{IH} o$	r V _{IL}	
	Off-State Current								$V_{OUT} = V_{CC}$ or GND		
I _{IN}	Input Leakage	0 - 5.5			±0.1	1	±1.0	μA	$V_{IN} = 5.5V$	or GND	
	Current										
I _{CC}	Quiescent Supply	5.5			4.0	1	40.0	μA	V _{IN} = V _{CC} or GND		
	Current										

Noise Characteristics

Symbol	Parameter	V _{CC} (V)	T _A =	25°C	Units	Conditions	
			Тур	Limits	onito	Conditions	
V _{OLP}	Quiet Output Maximum	5.0	0.5	0.8	V	C _L = 50 pF	
(Note 3)	Dynamic V _{OL}						
V _{OLV}	Quiet Output Minimum	5.0	-0.5	-0.8	V	C _L = 50 pF	
(Note 3)	Dynamic V _{OL}						
V _{IHD}	Minimum HIGH Level	5.0		3.5	V	C _L = 50 pF	
(Note 3)	Dynamic Input Voltage						
V _{ILD}	Maximum HIGH Level	5.0		1.5	V	C _L = 50 pF	
(Note 3)	Dynamic Input Voltage						

Note 3: Parameter guaranteed by design.

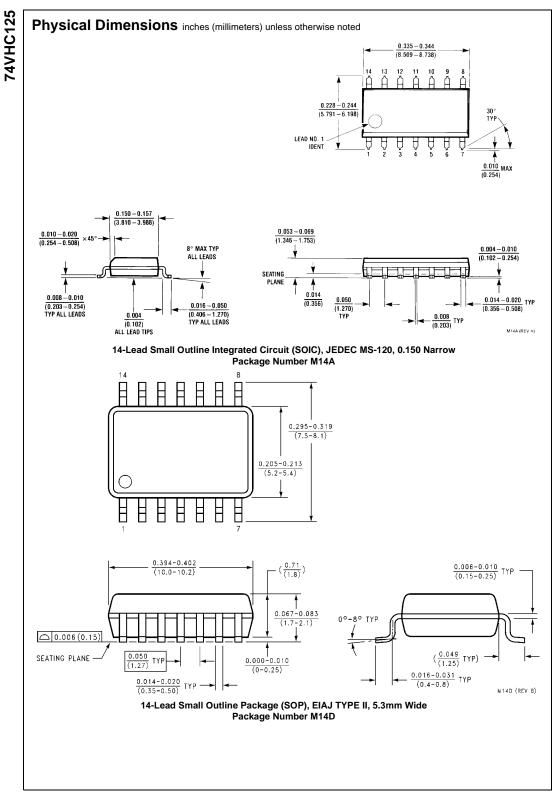
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Symbol	Parameter Propagation Delay	V _{CC}	$T_A = 25^{\circ}C$			$\textbf{T}_{\textbf{A}}=-\textbf{40}^{\circ}\textbf{C} \text{ to } +\textbf{85}^{\circ}\textbf{C}$		Units	Conditions	
		(V)	Min	Тур	Max	Min	Max	Units	Conditions	
		3.3 ± 0.3		5.6	8.0	1.0	9.5			$C_L = 15 \text{ pF}$
t _{PHL}	Time			8.1	11.5	1.0	13.0	ns		$C_L = 50 \text{ pF}$
		5.0 ± 0.5		3.8	5.5	1.0	6.5	ns		$C_L = 15 \text{ pF}$
				5.3	7.5	1.0	8.5	115		$C_L = 50 \text{ pF}$
t _{PZL}	3-STATE Output	3.3 ± 0.3		5.4	8.0	1.0	9.5	ns	$R_L = 1 \ k\Omega$	$C_L = 15 \text{ pF}$
t _{PZH}	Enable Time			7.9	11.5	1.0	13.0	115		$C_L = 50 \text{ pF}$
		5.0 ± 0.5		3.6	5.1	1.0	6.0			$C_L = 15 \text{ pF}$
				5.1	7.1	1.0	8.0	ns		$C_L = 50 \text{ pF}$
t _{PLZ}	3-STATE Output	3.3 ± 0.3		9.5	13.2	1.0	15.0	ns	$R_L = 1 k\Omega$	$C_L = 50 \text{ pF}$
t _{PHZ}	Disable Time	5.0 ± 0.5		6.1	8.8	1.0	10.0	115		$C_L = 50 \text{ pF}$
t _{OSLH}	Output to Output Skew	3.3 ± 0.3			1.5		1.5	ns	(Note 4)	$C_L = 50 \text{ pF}$
t _{OSHL}		5.0 ± 0.5			1.0		1.0	115		$C_L = 50 \text{ pF}$
CIN	Input Capacitance			4	10		10	pF	V _{CC} = Open	
C _{OUT}	Output Capacitance			6				pF	V _{CC} = 5.0\	/
C _{PD}	Power Dissipation			14				pF	(Note 5)	
	Capacitance									

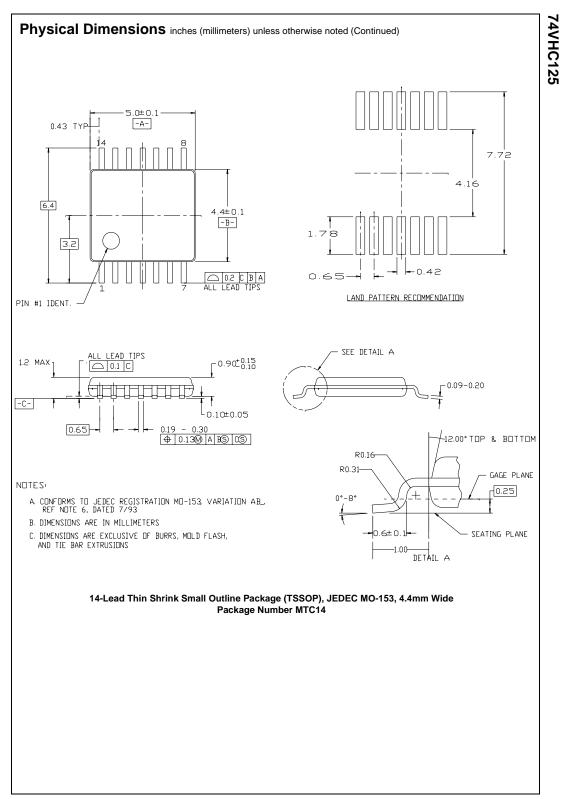
 $\textbf{Note 4:} \text{ Parameter guaranteed by design. } t_{OSLH} = |t_{PLHmax} - t_{PLHmin}|; \ t_{OSHL} = |t_{PHLmax} - t_{PHLmin}|.$

Note 5: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC} (OPR.) = $C_{PD} * V_{CC} * f_{IN} + I_{CC}/4$ (per bit).

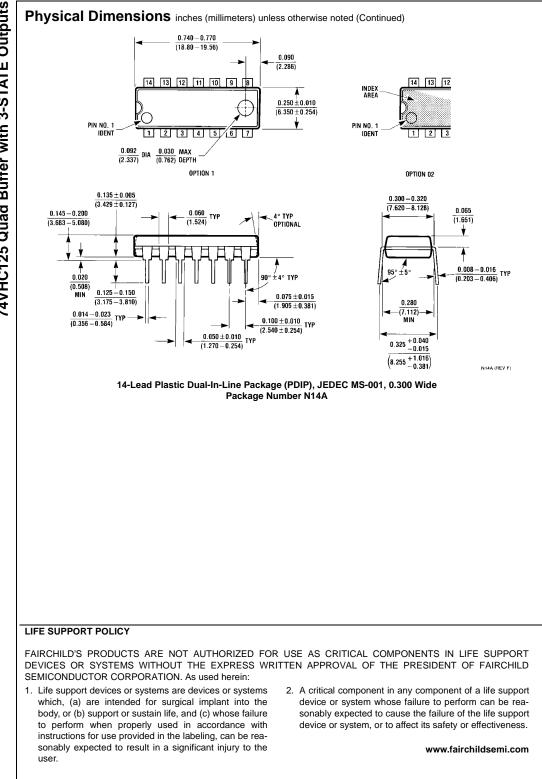
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